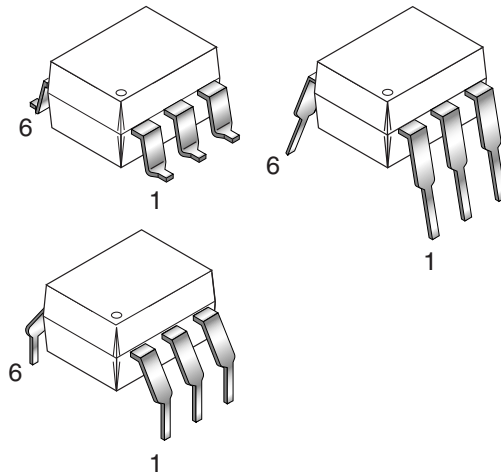


H11N1-M

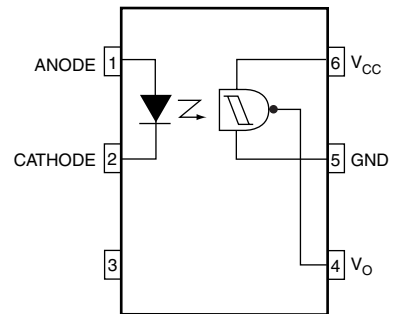
H11N2-M

H11N3-M

PACKAGE



SCHEMATIC



DESCRIPTION

The H11NX-M series has a high speed integrated circuit detector optically coupled to an AlGaAs infrared emitting diode. The output incorporates a Schmitt trigger, which provides hysteresis for noise immunity and pulse shaping. The detector circuit is optimized for simplicity of operation and utilizes an open collector output for maximum application flexibility.

FEATURES

- High data rate, 5 MHz typical (NRZ)
- Free from latch up and oscillation throughout voltage and temperature ranges.
- Microprocessor compatible drive
- Logic compatible output sinks 16 mA at 0.5 V maximum
- Guaranteed on/off threshold hysteresis
- Wide supply voltage capability, compatible with all popular logic systems
- High common mode transient immunity, 2000 V/ μ s minimum
- Fast switching $t_r = 7.5$ ns typical, $t_f = 12$ ns typical
- Underwriter Laboratory (UL) recognized—file #E90700
- VDE recognized – File#102497 – Add option V (e.g., H11N1VM)

APPLICATIONS

- Logic to logic isolator
- Programmable current level sensor
- Line receiver—eliminate noise and transient problems
- A.C. to TTL conversion—square wave shaping
- Interfaces computers with peripherals
- Isolated power MOS driver for power supplies

H11N1-M

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ABSOLUTE MAXIMUM RATINGS

Parameters	Symbol	Device	Value	Units
TOTAL DEVICE				
Storage Temperature	T _{STG}	All	-55 to +150	°C
Operating Temperature	T _{OPR}	All	-40 to +85	°C
Lead Solder Temperature	T _{SOL}	All	260 for 10 sec	°C
Total Device Power Dissipation @ 25°C Derate Above 25°C	P _D	All	250	mW
			2.94	mW/°C
EMITTER				
Continuous Forward Current	I _F	All	30	mA
Reverse Voltage	V _R	All	6	V
Forward Current - Peak (1 μs pulse, 300 pps)	I _{F(pk)}	All	1.0	A
LED Power Dissipation 25°C Ambient Derate Linearly From 25°C	P _D	All	120	mW
			1.41	mW/°C
DETECTOR				
Detector Power Dissipation @ 25°C Derate Linearly from 25°C	P _D	All	150	mW
			1.76	mW/°C
V ₄₅ Allowed Range	V _O	All	0 to 16	V
V ₆₅ Allowed Range	V _{CC}	All	0 to 16	V
I ₄ Output Current	I _O	All	50	mA

ELECTRICAL CHARACTERISTICS ($T_A = 0-70^\circ\text{C}$ Unless otherwise specified.)

INDIVIDUAL COMPONENT CHARACTERISTICS

Parameters	Test Conditions	Symbol	Device	Min	Typ*	Max	Units
EMITTER							
Input Forward Voltage	$I_F = 10\text{ mA}$	V_F	All		1.4	2	V
	$I_F = 0.3\text{ mA}$			0.75	1.25		
Reverse Current	$V_R = 5\text{ V}$	I_R	All			10	μA
Capacitance	$V = 0, f = 1.0\text{ MHz}$	C_J	All			100	pF
DETECTOR							
Operating Voltage Range		V_{CC}	All	4		15	V
Supply Current	$I_F = 0, V_{CC} = 5\text{ V}$	$I_{CC(off)}$	All		6	10	mA
Output Current, High	$I_F = 0.3\text{ mA}, V_{CC} = V_O = 15\text{ V}$	I_{OH}	All			100	μA

*Typical values at $T_A = 25^\circ\text{C}$

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TRANSFER CHARACTERISTICS

DC Characteristics	Test Conditions	Symbol	Device	Min	Typ*	Max	Units
Supply Current	$I_F = 10\text{mA}$, $V_{CC} = 5\text{V}$	$I_{CC(on)}$	All		6.5	10	mA
Output Voltage, low	$R_L = 270\Omega$, $V_{CC} = 5\text{V}$, $I_F = I_{F(on)}$ max.	V_{OL}	All			0.5	V
Turn-On Threshold Current	$R_L = 270\Omega$, $V_{CC} = 5\text{V}$ note 1	$I_{F(on)}$	H11N1-M	0.8		3.2	mA
			H11N2-M	2.3		5	
			H11N3-M	4.1		10	
Turn-Off Threshold Current	$R_L = 270\Omega$, $V_{CC} = 5\text{V}$	$I_{F(off)}$	All	0.3			mA
Hysteresis Ratio	$R_L = 270\Omega$, $V_{CC} = 5\text{V}$	$I_{F(off)}/I_{F(on)}$	All	0.65		0.95	
AC Characteristics	Test Conditions	Symbol	Device	Min	Typ	Max	Units
SWITCHING SPEED							
Propagation delay time High to Low	$C = 120\text{pF}$, $t_P = 1\mu\text{s}$, R_E : Note 2 Fig. 1	t_{PHL}	All		100	330	ns
Rise Time	$C = 120\text{pF}$, $t_P = 1\mu\text{s}$, R_E : Note 2 Fig. 1	t_r	All		7.5		ns
Propagation delay time Low to High	$C = 120\text{pF}$, $t_P = 1\mu\text{s}$, R_E : Note 2 Fig. 1	t_{PLH}	All		150	330	ns
Fall time	$C = 120\text{pF}$, $t_P = 1\mu\text{s}$, R_E : Note 2 Fig. 1	t_f	All		12		ns
Data Rate			All		5		MHz

ISOLATION CHARACTERISTICS

Parameters	Test Conditions	Symbol	Min	Typ*	Max	Units
Input-Output Isolation Voltage	$f = 60\text{ Hz}$, $t = 1\text{ sec.}$	V_{ISO}	7500			V_{PEAK}
Isolation Capacitance	$V_{I-O} = 0\text{V}$, $f = 1\text{ MHz}$	C_{ISO}		0.4	0.6	pF
Isolation Resistance	$V_{I-O} = \pm 500\text{ VDC}$	R_{ISO}	10^{11}			Ω

*Typical values at $T_A = 25^\circ\text{C}$

NOTES:

- Maximum $I_{F(ON)}$ is the maximum current required to trigger the output. For example, a 3.2mA maximum trigger current would require the LED to be driven at a current greater than 3.2mA to guarantee the device will turn on. A 10% guard band is recommended to account for degradation of the LED over its lifetime. The maximum allowable LED drive current is 30mA.
- H11N1: $R_E = 910\Omega$
H11N2: $R_E = 560\Omega$
H11N3: $R_E = 240\Omega$

H11N1-M

H11N2-M

H11N3-M

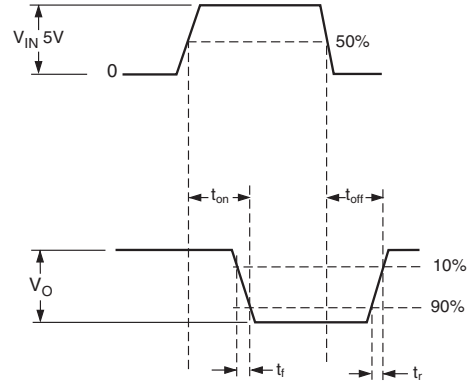
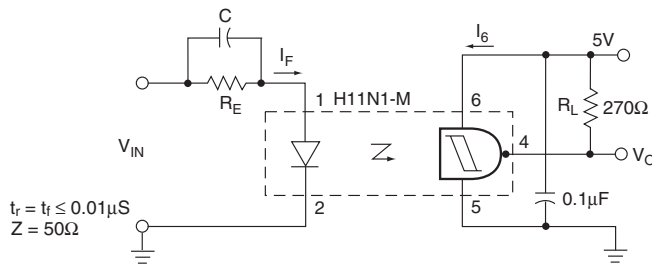


Figure 1. Switching Test Circuit and Waveforms

Figure 2. Transfer Characteristics

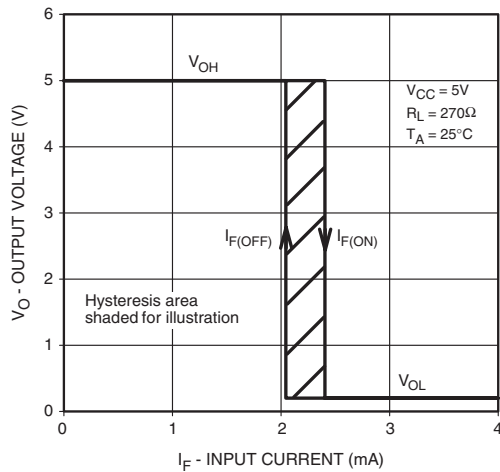


Figure 3. Threshold Current vs. Supply Voltage

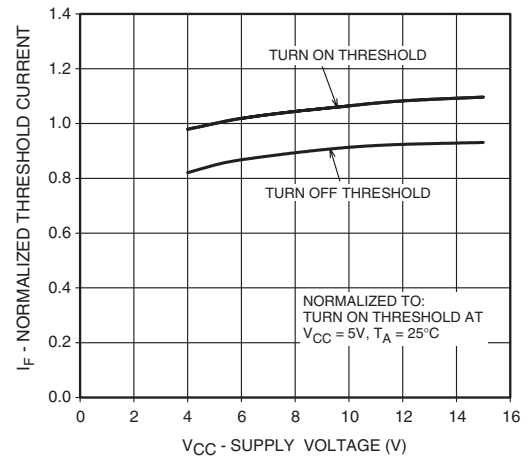


Figure 4. Threshold Current vs. Temperature

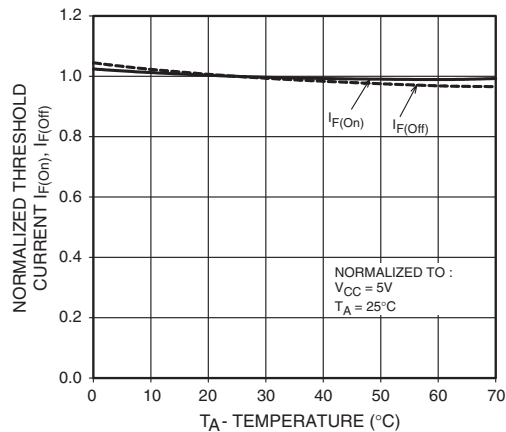
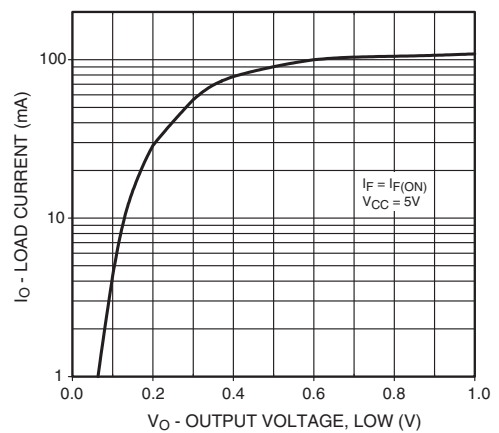


Figure 5. Load Current vs. Output Voltage



H11N1-M

H11N2-M

H11N3-M

Figure 6. Supply Current vs. Supply Voltage

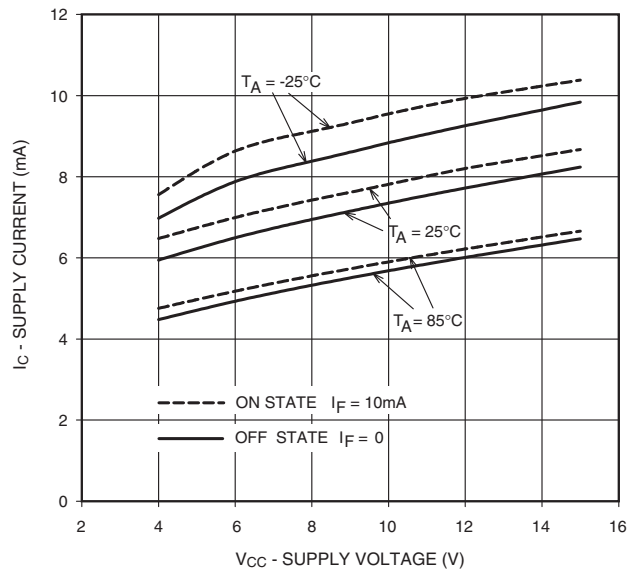
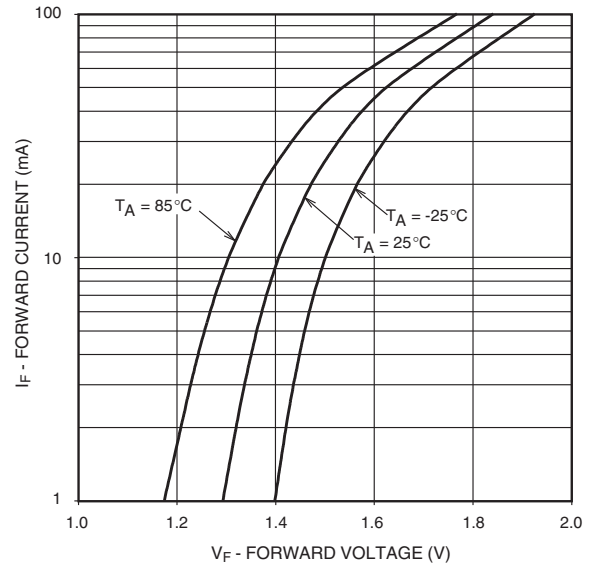


Figure 7. LED Forward Voltage vs. Forward Current



H11N1-M

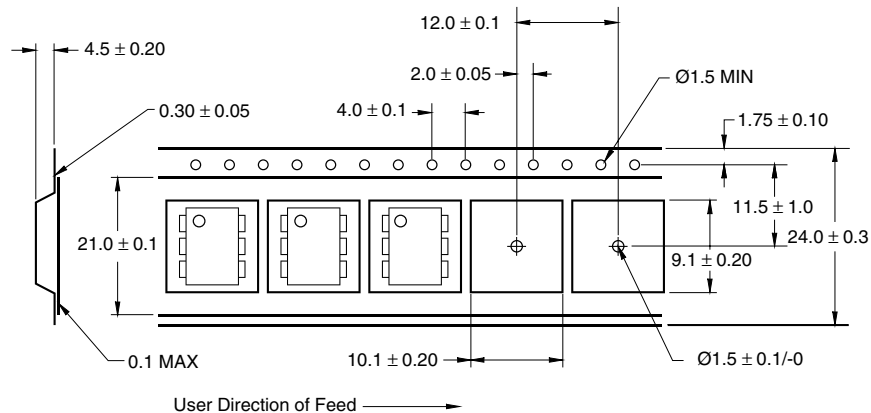
H11N2-M

H11N3-M

ORDERING INFORMATION

Option/Order Entry Identifier	Description
S	Surface Mount Lead Bend
SR2	Surface Mount; Tape and reel
T	0.4" Lead Spacing
V	VDE 0884
TV	VDE 0884, 0.4" Lead Spacing
SV	VDE 0884, Surface Mount
SR2V	VDE 0884, Surface Mount, Tape & Reel

Carrier Tape Specifications



NOTE

All dimensions are in inches (millimeters)

H11N1-M

H11N2-M

H11N3-M

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2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.